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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	Unknown	
(Use as many sheets as necessary)	Filing Date	Even Date Herewith	
	First Named Inventor	Geusic, Joseph	
	Group Art Unit	Unknown 2823	
	Examiner Name	Unknown MAldonado. J	
Sheet 1 of 4	Attorney Docket No: 3	303.390US4	

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	First Named Inventor	Geusic, Joseph		
	Group Art Unit	Unknown		
	Examiner Name	Unknown		
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Substitute for form 1449APTO	Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	Unknown	
(Use as many sheels as necessary)	Filing Date	Even Date Herewith	
	First Named Inventor	Geusic, Joseph	
	Group Art Unit	Unknown	
	Examiner Name	Unknown	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	Unknown	
(Use as many sheets as necessary)	Filing Date	Even Date Herewith	
	First Named Inventor	Geusic, Joseph	
	Group Art Unit	Unknown	
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for form 1449A/PTO Complete if Known RMATION DISCLOSURE 10/772,606 **Application Number** TATEMENT BY APPLICANT February 5, 2004 Filing Date (Use as many sheets as necessary) Geusic, Joseph **First Named Inventor** 2823 **Group Art Unit** Maldonado, Julio **Examiner Name** Attorney Docket No: 303.390US4 Sheet 1 of 1

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